

MOSFET

Metal Oxide Semiconductor Field Effect Transistor

CoolMOS™ CE

500V CoolMOS™ CE Power Transistor
IPx50R1K4CE

Data Sheet

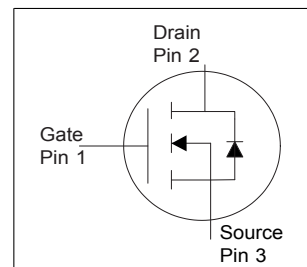
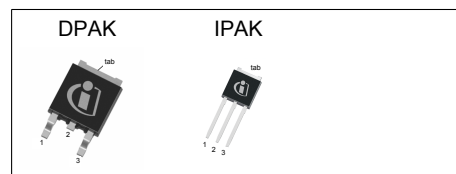
Rev. 2.2
Final

1 Description

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ CE series combines the experience of the leading SJ MOSFET supplier with high class innovation while representing a cost appealing alternative compared to standard MOSFETs in target applications. The resulting devices provide all benefits of a fast switching SJ MOSFET while not sacrificing ease of use. Extremely low switching and conduction losses make switching applications even more efficient, more compact, lighter and cooler.

Features ¹⁾

- Extremely low losses due to very low FOM $R_{DS(on)} \cdot Q_g$ and E_{oss}
- Very high commutation ruggedness
- Easy to use/drive
- Qualified for industrial grade applications according to JEDEC (J-STD20 and JESD22)
- Pb-free plating, available with halogen free and non-halogen free mold compound¹⁾



Applications

PFC stages, hard switching PWM stages and resonant switching PWM stages for e.g. PC Silverbox, LCD & PDP TV and Lighting.



Table 1 Key Performance Parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	550	V
$R_{DS(on),max}$	1.4	Ω
$Q_{g,typ}$	8.2	nC
$I_{D,pulse}$	8.8	A
$E_{oss@400V}$	0.79	μJ
Body diode di/dt	500	A/ μs

Type / Ordering Code	Package	Marking	Related Links
IPD50R1K4CE	PG-TO 252	5R1K4CE	see Appendix A
IPU50R1K4CE	PG-TO 251		

¹⁾ Halogen free version is available with OPN: IPD50R1K4CEAT

Table of Contents

Description	2
Maximum ratings	4
Thermal characteristics	4
Electrical characteristics	5
Electrical characteristics diagrams	7
Test Circuits	11
Package Outlines	12
Appendix A	14
Revision History	15
Disclaimer	15

2 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	3.1 1.9	A	$T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$
Pulsed drain current ²⁾	$I_{D,pulse}$	-	-	8.8	A	$T_C = 25^\circ\text{C}$
Avalanche energy, single pulse	E_{AS}	-	-	49	mJ	$I_D = 1.1\text{A}$; $V_{DD} = 50\text{V}$
Avalanche energy, repetitive	E_{AR}	-	-	0.07	mJ	$I_D = 1.1\text{A}$; $V_{DD} = 50\text{V}$
Avalanche current, repetitive	I_{AR}	-	-	1.1	A	-
MOSFET dv/dt ruggedness	dv/dt	-	-	50	V/ns	$V_{DS} = 0 \dots 400\text{V}$
Gate source voltage	V_{GS}	-20 -30	-	20 30	V	static; AC ($f > 1\text{ Hz}$)
Power dissipation (non FullPAK) TO-252, TO-251	P_{tot}	-	-	25	W	$T_C = 25^\circ\text{C}$
Operating and storage temperature	T_j, T_{stg}	-55	-	150	$^\circ\text{C}$	-
Continuous diode forward current	I_S	-	-	2.6	A	$T_C = 25^\circ\text{C}$
Diode pulse current ²⁾	$I_{S,pulse}$	-	-	8.8	A	$T_C = 25^\circ\text{C}$
Reverse diode dv/dt ³⁾	dv/dt	-	-	15	V/ns	$V_{DS} = 0 \dots 400\text{V}$, $I_{SD} \leq I_S$, $T_j = 25^\circ\text{C}$, $t_{cond} < 2\mu\text{s}$
Maximum diode commutation speed ³⁾	di/dt	-	-	500	A/ μs	$V_{DS} = 0 \dots 400\text{V}$, $I_{SD} \leq I_S$, $T_j = 25^\circ\text{C}$, $t_{cond} < 2\mu\text{s}$

3 Thermal characteristics

Table 3 Thermal characteristics DPAK, IPAK

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	4.91	$^\circ\text{C/W}$	-
Thermal resistance, junction - ambient ⁴⁾	R_{thJA}	-	- 35	62 -	$^\circ\text{C/W}$	SMD version, device on PCB, minimal footprint SMD version, device on PCB, 6cm ² cooling area ⁴⁾
Soldering temperature, wave- & reflowsoldering allowed	T_{sold}	-	-	260	$^\circ\text{C}$	reflow MSL 1

¹⁾ Limited by $T_{j,max}$. Maximum duty cycle $D=0.75$

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ $V_{DClamp}=400\text{V}$; $V_{DS,peak} < V_{(BR)DSS}$; identical low side and high side switch with identical R_G

⁴⁾ Device on 40mm*40mm*1.5mm one layer epoxy PCB FR4 with 6cm² copper area (thickness 70 μm) for drain connection. PCB is vertical without air stream cooling.

4 Electrical characteristics

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	500	-	-	V	$V_{GS}=0V, I_D=1mA$
Gate threshold voltage	$V_{(GS)th}$	2.50	3	3.50	V	$V_{DS}=V_{GS}, I_D=0.07mA$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS}=500V, V_{GS}=0V, T_j=25^\circ C$ $V_{DS}=500V, V_{GS}=0V, T_j=150^\circ C$
Gate-source leakage current	I_{GSS}	-	-	100	nA	$V_{GS}=20V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	1.26 3.28	1.40 -	Ω	$V_{GS}=13V, I_D=0.9A, T_j=25^\circ C$ $V_{GS}=13V, I_D=0.9A, T_j=150^\circ C$
Gate resistance	R_G	-	7	-	Ω	$f=1\text{ MHz, open drain}$

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	178	-	pF	$V_{GS}=0V, V_{DS}=100V, f=1MHz$
Output capacitance	C_{oss}	-	11	-	pF	$V_{GS}=0V, V_{DS}=100V, f=1MHz$
Effective output capacitance, energy related ¹⁾	$C_{o(er)}$	-	10	-	pF	$V_{GS}=0V, V_{DS}=0...400V$
Effective output capacitance, time related ²⁾	$C_{o(tr)}$	-	36	-	pF	$I_D=\text{constant}, V_{GS}=0V, V_{DS}=0...400V$
Turn-on delay time	$t_{d(on)}$	-	6.5	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=1.1A, R_G=5.3\Omega$
Rise time	t_r	-	6	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=1.1A, R_G=5.3\Omega$
Turn-off delay time	$t_{d(off)}$	-	23	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=1.1A, R_G=5.3\Omega$
Fall time	t_f	-	30	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=1.1A, R_G=5.3\Omega$

Table 6 Gate charge characteristics

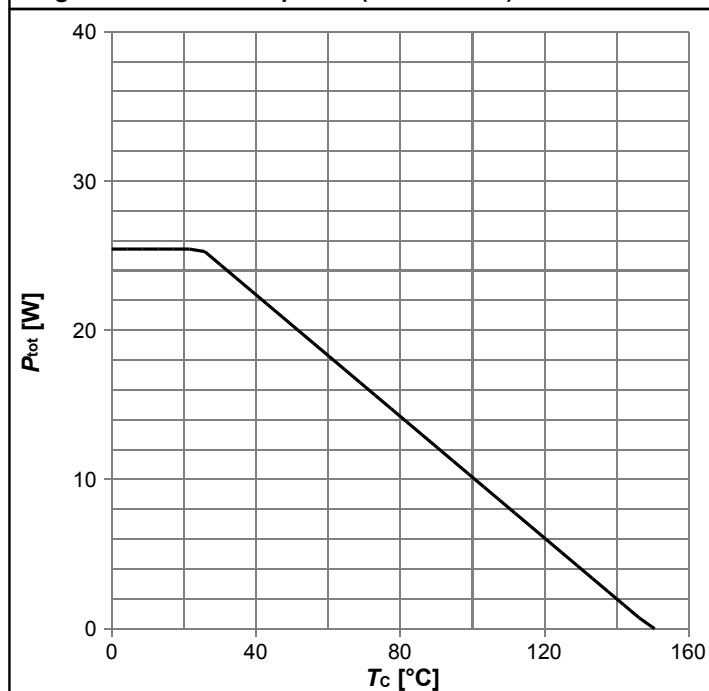
Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	1	-	nC	$V_{DD}=400V, I_D=1.1A, V_{GS}=0\text{ to }10V$
Gate to drain charge	Q_{gd}	-	4.6	-	nC	$V_{DD}=400V, I_D=1.1A, V_{GS}=0\text{ to }10V$
Gate charge total	Q_g	-	8.2	-	nC	$V_{DD}=400V, I_D=1.1A, V_{GS}=0\text{ to }10V$
Gate plateau voltage	$V_{plateau}$	-	5.4	-	V	$V_{DD}=400V, I_D=1.1A, V_{GS}=0\text{ to }10V$

¹⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$
²⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$

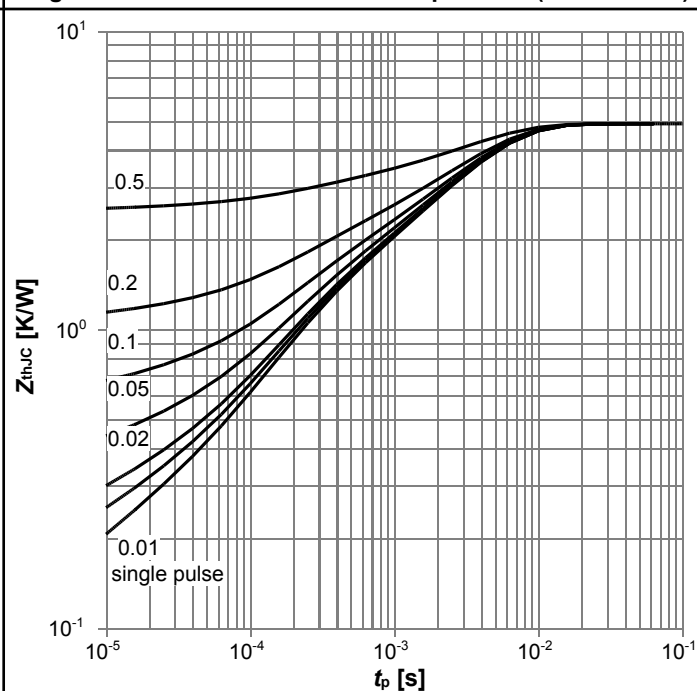
Table 7 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.83	-	V	$V_{GS}=0V$, $I_F=1.1A$, $T_f=25^{\circ}C$
Reverse recovery time	t_{rr}	-	120	-	ns	$V_R=400V$, $I_F=1.1A$, $di_F/dt=100A/\mu s$
Reverse recovery charge	Q_{rr}	-	0.5	-	μC	$V_R=400V$, $I_F=1.1A$, $di_F/dt=100A/\mu s$
Peak reverse recovery current	I_{rrm}	-	6.8	-	A	$V_R=400V$, $I_F=1.1A$, $di_F/dt=100A/\mu s$

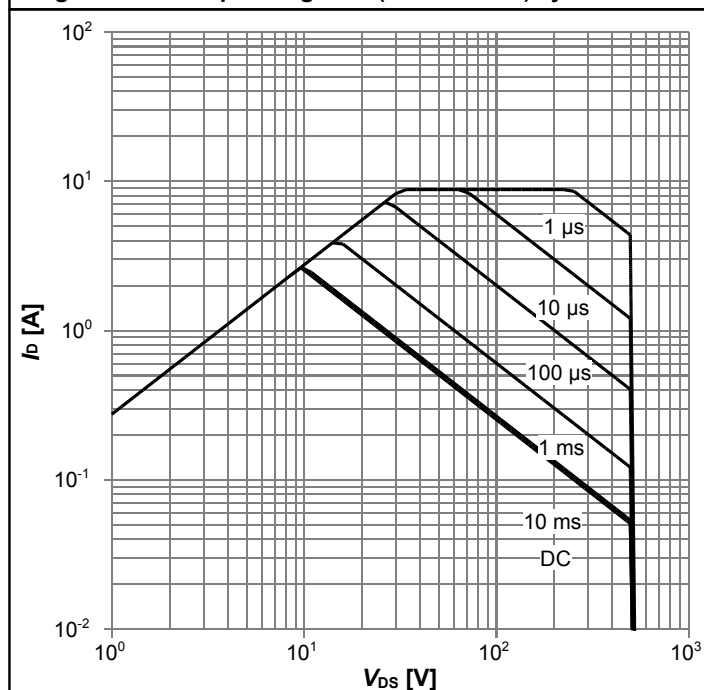
5 Electrical characteristics diagrams

Diagram 1: Power dissipation (Non FullPak)


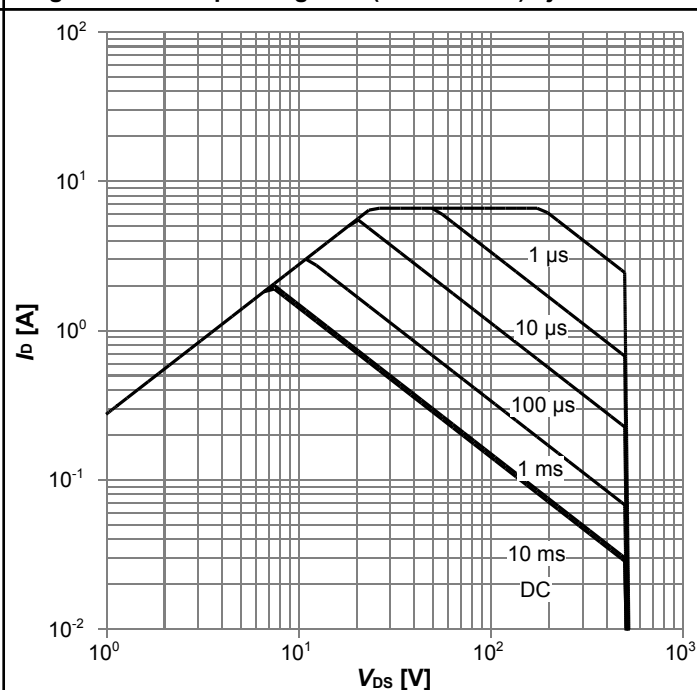
$$P_{\text{tot}} = f(T_c)$$

Diagram 2: Max. transient thermal impedance (Non FullPak)


$$Z_{\text{thJC}} = f(t_p); \text{ parameter: } D = t_p / T$$

Diagram 3: Safe operating area (Non FullPak) $T_j = 25^\circ\text{C}$


$$I_D = f(V_{\text{DS}}); T_c = 25^\circ\text{C}; D = 0; \text{ parameter: } t_p$$

Diagram 4: Safe operating area (Non FullPak) $T_j = 80^\circ\text{C}$


$$I_D = f(V_{\text{DS}}); T_c = 80^\circ\text{C}; D = 0; \text{ parameter: } t_p$$

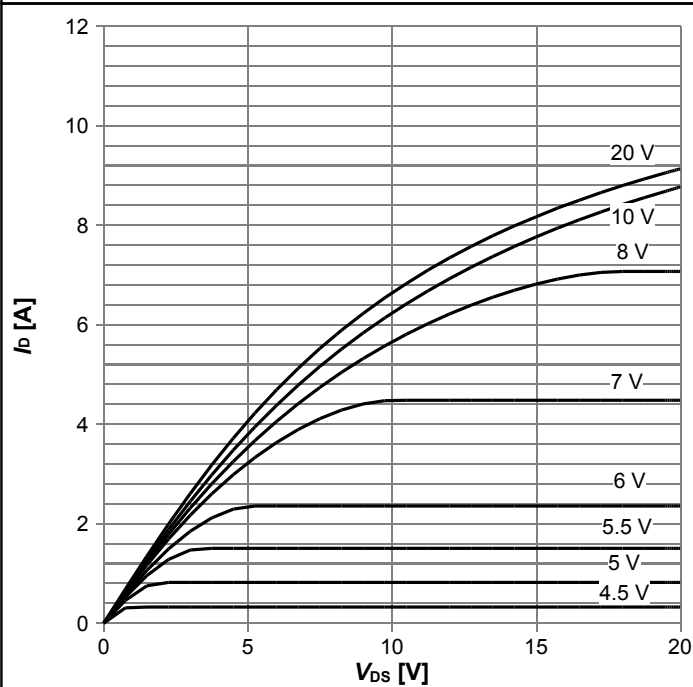
Diagram 5: Typ. output characteristics $T_j=25^\circ\text{C}$

 $I_D=f(V_{DS}); T_j=25^\circ\text{C}; \text{parameter: } V_{GS}$

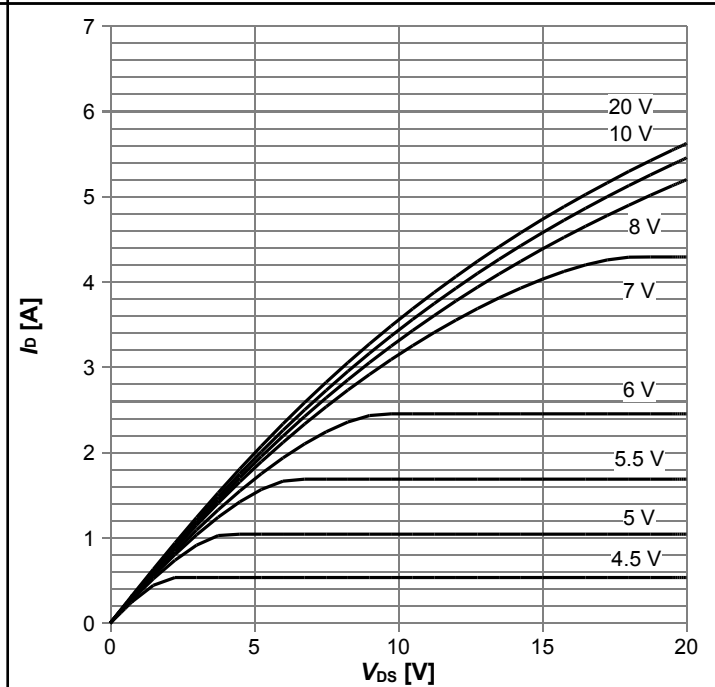
Diagram 6: Typ. output characteristics $T_j=125^\circ\text{C}$

 $I_D=f(V_{DS}); T_j=125^\circ\text{C}; \text{parameter: } V_{GS}$

Diagram 7: Typ. drain-source on-state resistance

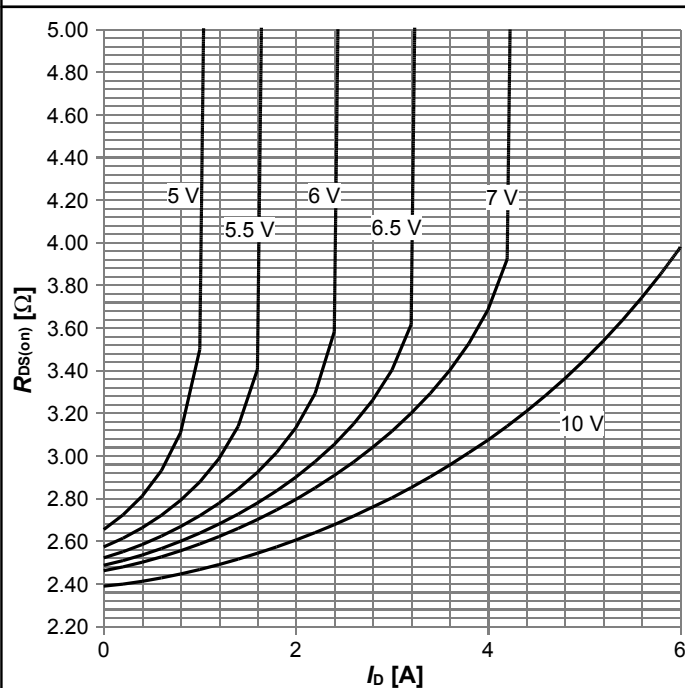

 $R_{DS(on)}=f(I_D); T_j=125^\circ\text{C}; \text{parameter: } V_{GS}$

Diagram 8: Drain-source on-state resistance

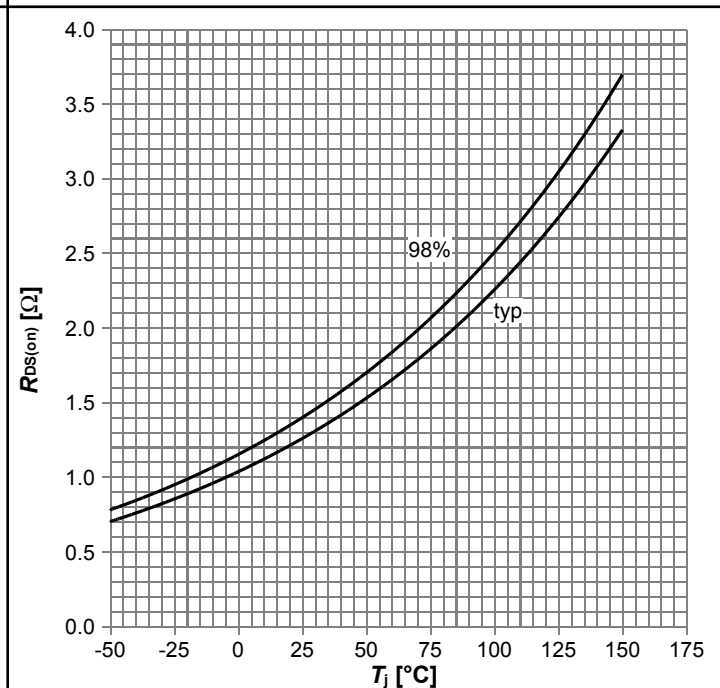

 $R_{DS(on)}=f(T_j); I_D=0.9\text{ A}; V_{GS}=13\text{ V}$

Diagram 9: Typ. transfer characteristics

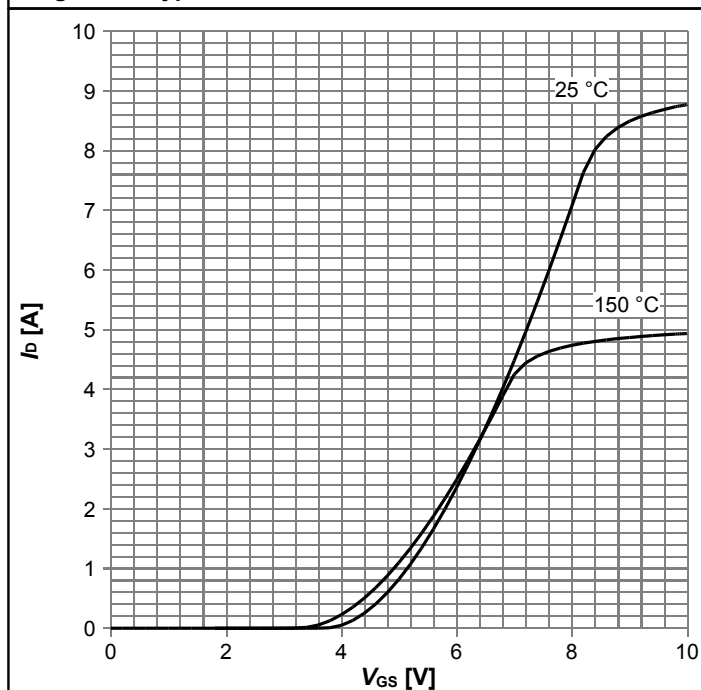

 $I_D = f(V_{GS})$; $V_{DS} = 20\text{ V}$; parameter: T_j

Diagram 10: Typ. gate charge

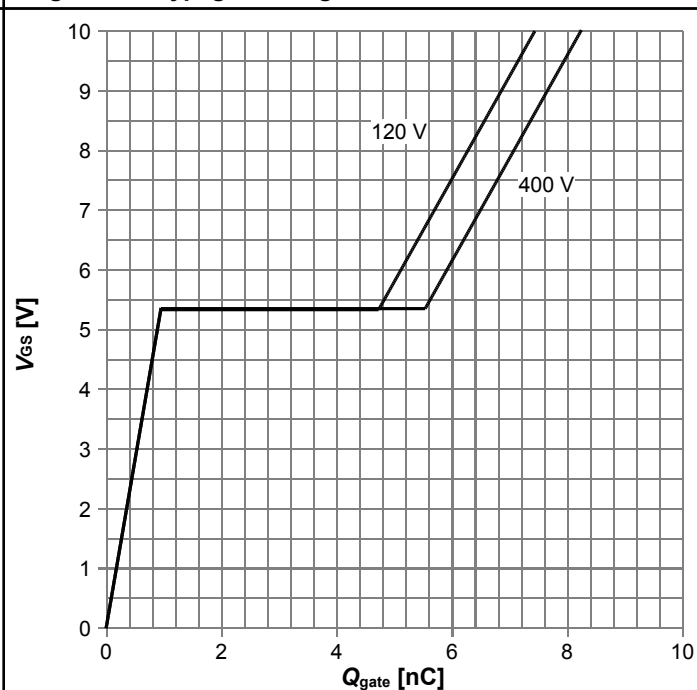

 $V_{GS} = f(Q_{gate})$; $I_D = 1.1\text{ A}$ pulsed; parameter: V_{DD}

Diagram 11: Avalanche energy

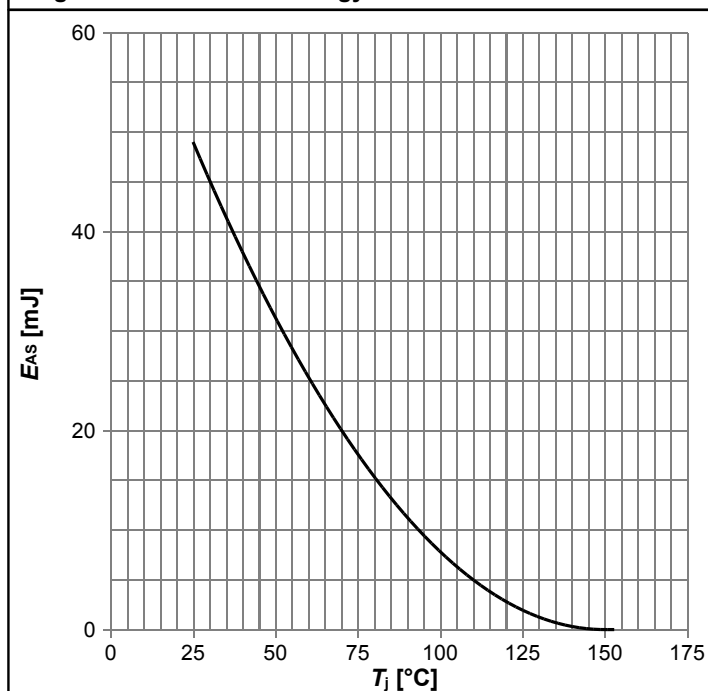

 $E_{AS} = f(T_j)$; $I_D = 1.1\text{ A}$; $V_{DD} = 50\text{ V}$

Diagram 12: Drain-source breakdown voltage

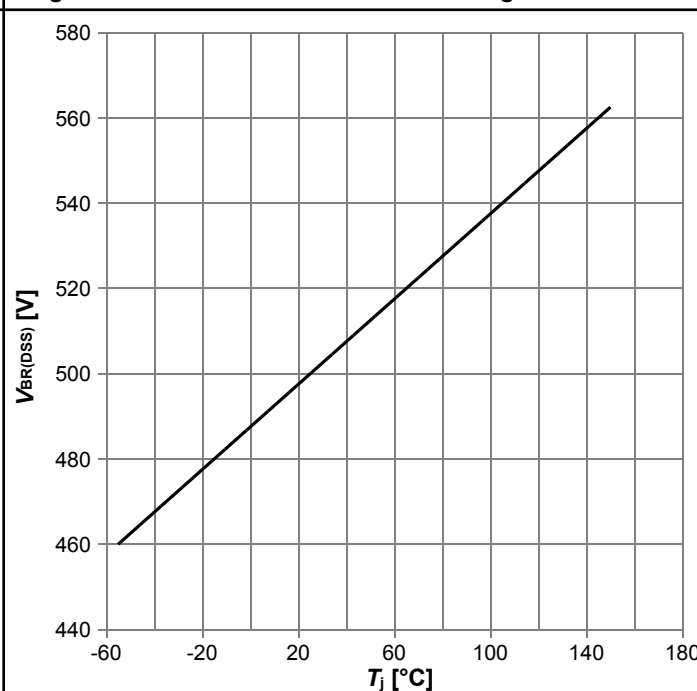
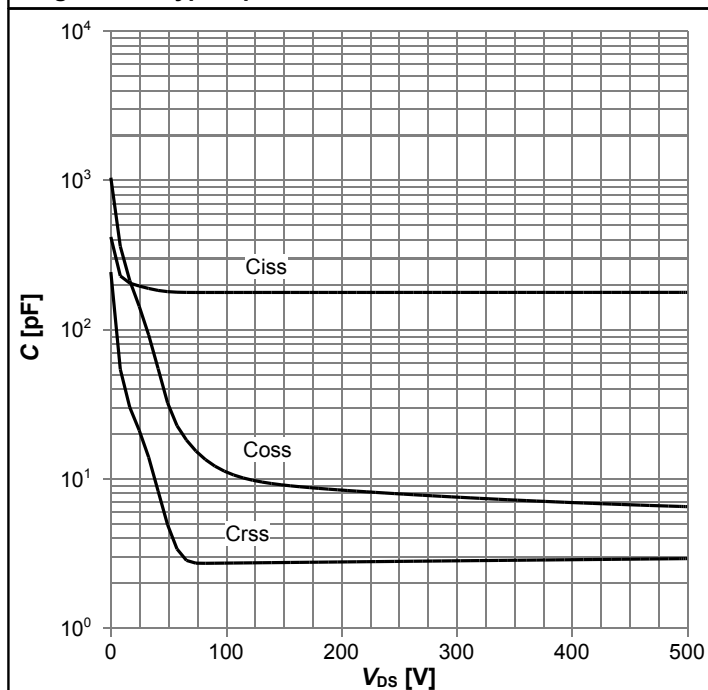
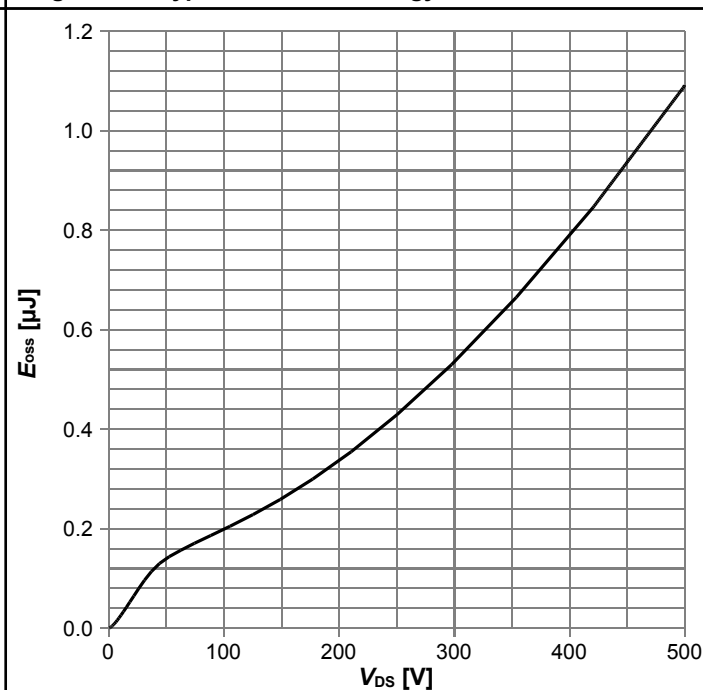

 $V_{BR(DSS)} = f(T_j)$; $I_D = 1\text{ mA}$

Diagram 13: Typ. capacitances



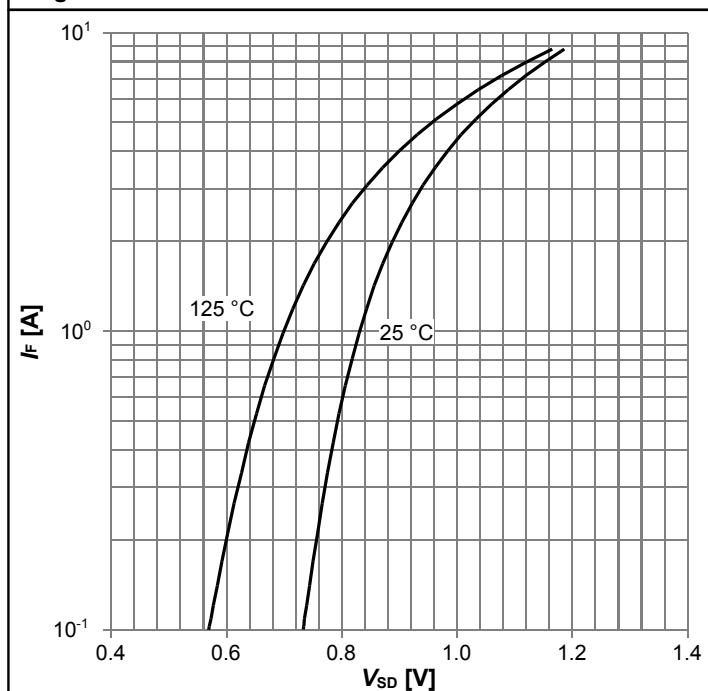
$$C=f(V_{DS}); V_{GS}=0 \text{ V}; f=1 \text{ MHz}$$

Diagram 14: Typ. Coss stored energy



$$E_{oss}=f(V_{DS})$$

Diagram 15: Forward characteristics of reverse diode



$$I_F=f(V_{SD}); \text{ parameter: } T_j$$

6 Test Circuits

Table 8 Diode characteristics

Test circuit for diode characteristics $R_{g1} = R_{g2}$	Diode recovery waveform $t_{rr} = t_F + t_S$ $Q_r = Q_F + Q_S$
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Table 9 Switching times

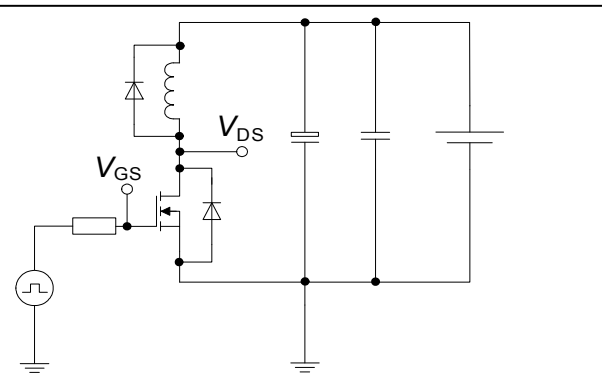
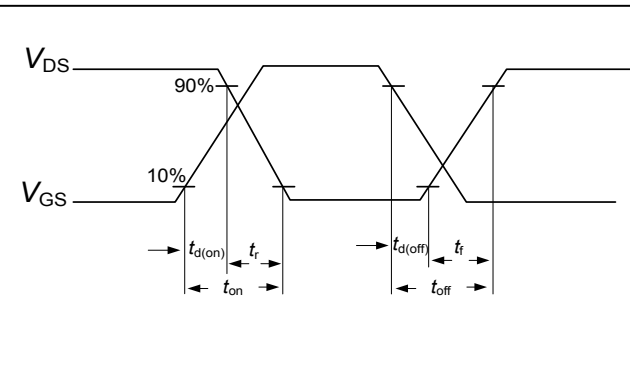
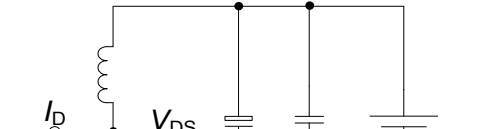
Switching times test circuit for inductive load	Switching times waveform
 The circuit diagram illustrates a switching test setup for an inductive load. A MOSFET is driven by a pulse generator connected to its gate through a resistor. The drain of the MOSFET is connected to an inductive load (represented by an inductor and a diode in parallel) and a load capacitor. The source of the MOSFET is connected to ground. The drain-source voltage (V_{DS}) and gate-source voltage (V_{GS}) are indicated for measurement.	 The timing diagram shows the switching waveforms for V_{DS} and V_{GS}. The diagram illustrates the turn-on and turn-off transitions. Key time intervals are marked: $t_{d(on)}$: Delay time from gate voltage rise to drain voltage fall. t_r: Rise time of the drain voltage during turn-on. t_{on}: Total turn-on time. $t_{d(off)}$: Delay time from gate voltage fall to drain voltage rise. t_f: Fall time of the drain voltage during turn-off. t_{off}: Total turn-off time.

Table 10 Unclamped inductive load

Unclamped inductive load test circuit	Unclamped inductive waveform
	

7 Package Outlines

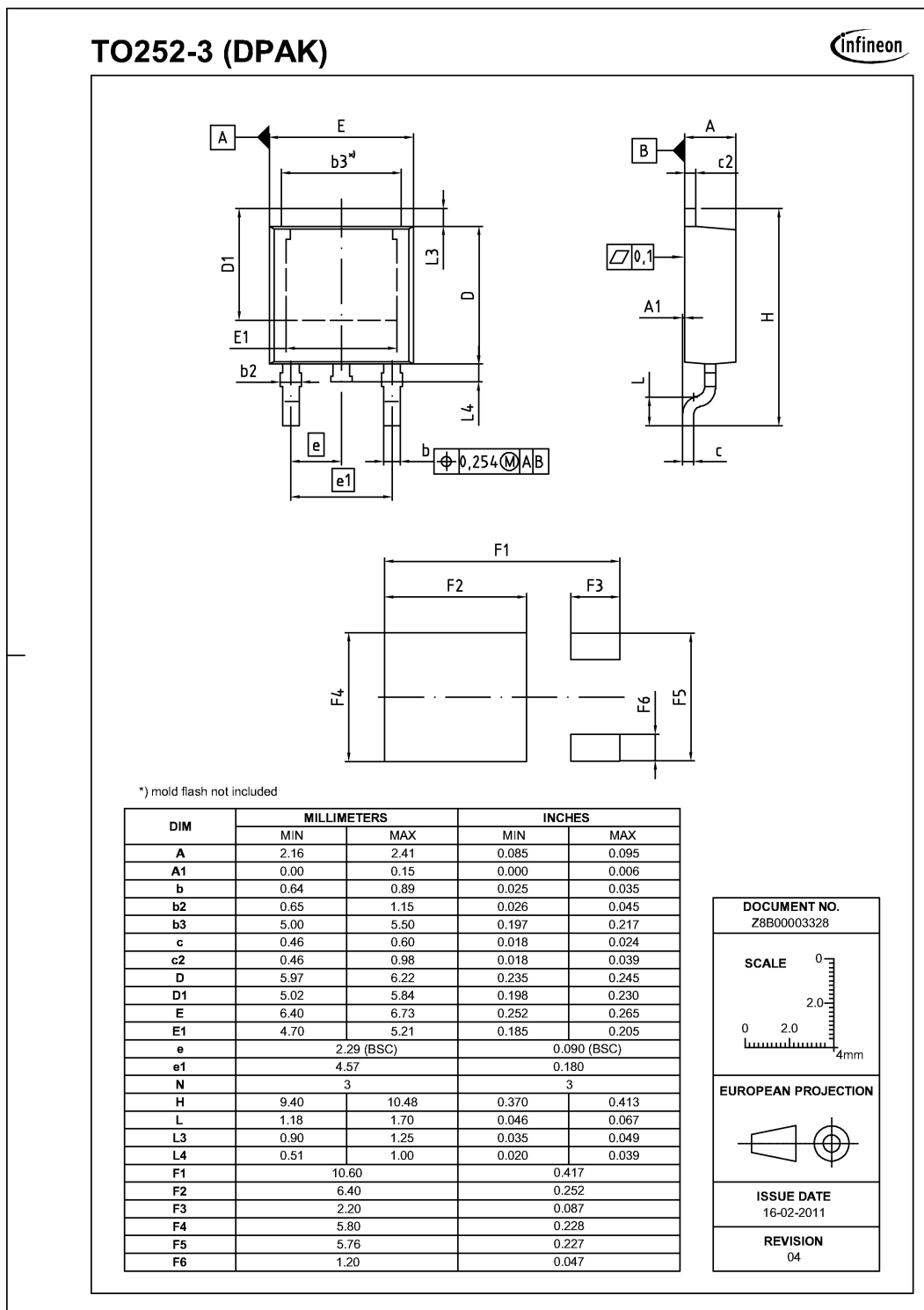
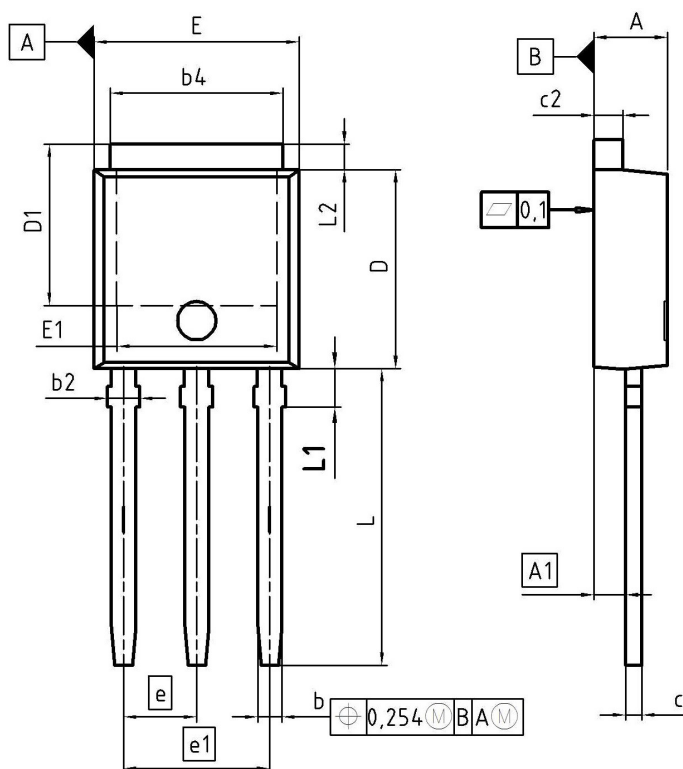


Figure 1 Outline PG-TO 252, dimensions in mm/inches



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.16	2.41	0.085	0.095
A1	0.90	1.14	0.035	0.045
b	0.64	0.89	0.025	0.035
b2	0.65	1.15	0.026	0.045
b4	4.95	5.50	0.195	0.217
c	0.46	0.60	0.018	0.024
c2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	5.04	5.77	0.198	0.227
E	6.35	6.73	0.250	0.265
E1	4.70	5.21	0.185	0.205
e	2.29		0.090	
e1	4.57		0.180	
N	3		3	
L	8.89	9.65	0.350	0.380
L1	1.90	2.29	0.075	0.090
L2	0.89	1.37	0.035	0.054

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Figure 2 Outline PG-TO 251, dimensions in mm/inches

8 Appendix A

Table 11 Related Links

- IFX CoolMOS Webpage: www.infineon.com
- IFX Design tools: www.infineon.com

Revision History

IPD50R1K4CE, IPU50R1K4CE

Revision: 2013-07-16, Rev. 2.2

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2012-09-13	Release of final version
2.1	2012-12-05	release of final datasheet
2.2	2013-07-16	update to Halogen free mold compound

We Listen to Your Comments

Any information within this document that you feel is wrong, unclear or missing at all? Your feedback will help us to continuously improve the quality of this document. Please send your proposal (including a reference to this document) to:

erratum@infineon.com

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